



DOCKET NO. 99-039

RESPONSE UNDER 37 C.F.R. 1.116-  
EXPEDITED PROCEDURE  
EXAMINING GROUP 1765

#17/B  
la  
9/30/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: : Sheldon Aronowitz, Valeriy Sukharev, John Haywood, James P. Kimball,  
Helmut Puchner, Ravindra Manohar Kapre, and Nicholas Eib

Appl. No. : 09/464,297

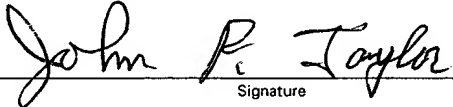
Filed: : December 15, 1999

Title : PROCESS FOR ETCHING A CONTROLLABLE THICKNESS OF  
OXIDE ON AN INTEGRATED CIRCUIT STRUCTURE ON A  
SEMICONDUCTOR SUBSTRATE USING NITROGEN PLASMA AND  
AN RF BIAS APPLIED TO THE SUBSTRATE

Grp./ A.U. : 1765

Examiner : Charlotte A. Brown

Docket No. : 99-039

CERTIFICATE OF MAILING	
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231	
o	September 20, 2002 (Date of Deposit)
John P. Taylor, Reg. No. 22,369	
 Signature	
September 20, 2002 Date of Signature	

AMENDMENT

Honorable Commissioner for Patents  
Washington, D.C. 20231

RECEIVED

SEP 30 2002

TC 1700

Date: September 20, 2002

Sir:

In response to the Final Rejection mailed July 31, 2002, please amend the application as follows: